

Silicon NPN Power Transistors

2SD1479

DESCRIPTION

- With TO-3PN package
- High voltage ,high reliability
- High speed switching
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

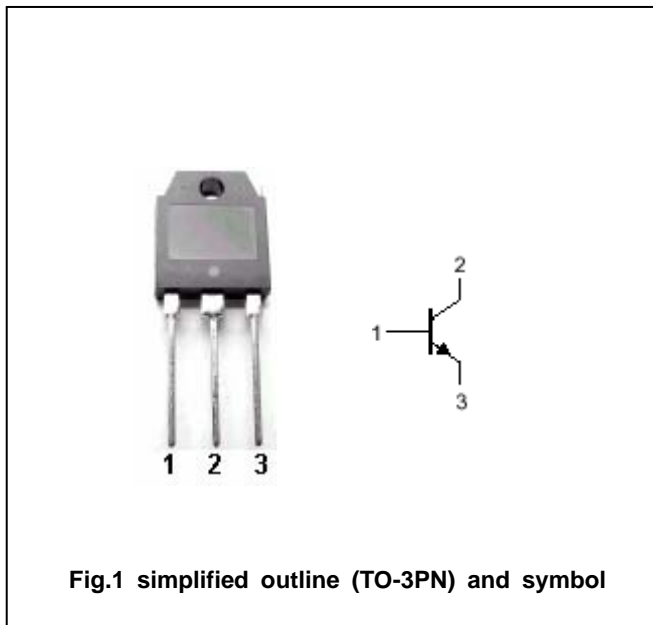


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	700	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		2.5	A
I_{CM}	Collector current (Pulse)		6	A
I_{BM}	Base current (Pulse)		2.5	A
P_C	Collector power dissipation	$T_C=25$	80	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =1A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =1A			1.5	V
I _{CBO}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μA
		V _{CB} =1500V; I _E =0			1.0	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			50	μA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	2		5	
t _s	Storage time	I _C =2.5A I _{Bend} =1.1A, L _B =10 μH			9.0	μs
t _f	Fall time				1.0	μs

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PACKAGE OUTLINE

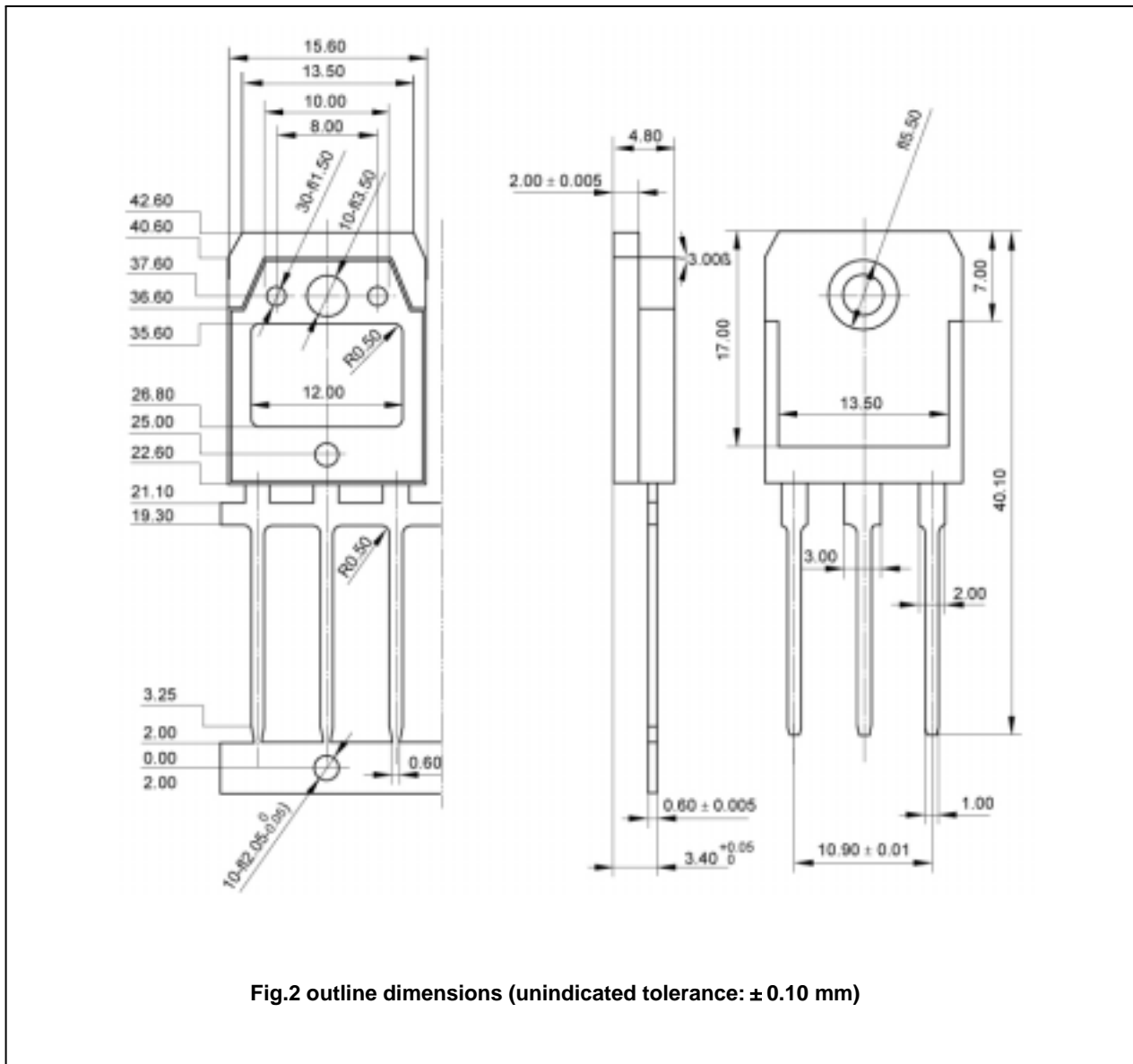


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)